

Description

This 60V 123A N-Channel MOSFET in a PDFN5×6 Plastic Package.

Features

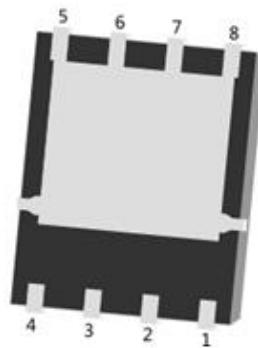
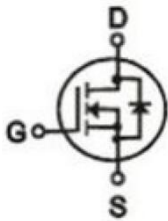
- Low $R_{DS(ON)}$ to minimize conductive loss
- low gate charge for fast switching
- Low thermal resistance
- Halogen-free product.

Applications

- Battery management
- High frequency point-of-load synchronous buck converter for MB/NB/UMPC/VGA
- Networking DC-DC power system
- Load switch

V_{DSS}	$R_{DS(ON)}$ Typ	I_D
60 V	2.8m Ω	123A

Equivalent Circuit & Pinning



Pin	极性
1	S
2	S
3	S
4	G
5	D
6	D
7	D
8	D

PIN1、2、3: S PIN4: G PIN5、6、7、8: D

Electrical Characteristics($T_a=25^{\circ}\text{C}$)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Turn-On Delay Time	$t_{d(on)}$	$V_{GS}=10\text{V}$ $V_{DS}=30\text{V}$ $R_L=1.5\ \Omega$ $R_{GEN}=3\ \Omega$		11		ns
Turn-On Rise Time	t_r			6		
Turn-Off Delay Time	$t_{d(off)}$			43		
Turn-Off Fall Time	t_f			2		

Absolute Maximum Ratings(Ta=25°C)

Parameter		Symbol	Rating	Unit
Drain-Source Voltage		V_{DS}	60	V
Continuous Drain Current		I_D	123	A
Pulsed Drain Current		I_{DM}	253	A
Gate-Source Voltage		V_{GS}	± 20	V
Power Dissipation		$P_D(T_c=25^\circ\text{C})$	83	W
Avalanche energy(L=0.5mH)		E_{AS}	2000	mJ
Avalanche Current(L=0.5mH)		I_{AS}	47	A
Junction and Storage Temperature Range		T_j, T_{stg}	-55 to 150	°C
Maximum Junction-to-Ambient	$t \leq 10s$	$R_{\theta JA}$	20	°C/W
	Steady-State		50	
Maximum Junction-to-Case	Steady-State	$R_{\theta JC}$	1.5	

Electrical Characteristics(Ta=25°C)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	BV_{DSS}	$I_D=250\mu A, V_{GS}=0V$	60	77		V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=60V, V_{GS}=0V$			1.0	μA
Gate-Body leakage current	I_{GSS}	$V_{DS}=0V, V_{GS}=\pm 20V$			± 100	nA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	1	1.6	2.5	V
Static Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS}=10V, I_D=20A$		2.8	3	m Ω
		$V_{GS}=4.5V, I_D=20A$		3.8	5	
Diode Forward Voltage	V_{SD}	$I_S=1A, V_{GS}=0V$		0.64	1	V
Input Capacitance	C_{iss}	$V_{DS}=25V, V_{GS}=0V, f=1.0MHz$		3710		pF
Output Capacitance	C_{oss}			2100		
Reverse Transfer Capacitance	C_{rss}			230		
Gate resistance	R_g	$V_{GS}=0V, V_{DS}=0V, f=1MHz$		2.3		Ω
Total Gate Charge	$Q_{g(10V)}$	$V_{GS}=10V, V_{DS}=30V, I_D=20A$		51		nC
Total Gate Charge	$Q_{g(4.5V)}$			25		
Gate Source Charge	Q_{gs}			10		
Gate Drain Charge	Q_{gd}			8.5		

Electrical Characteristic Curve

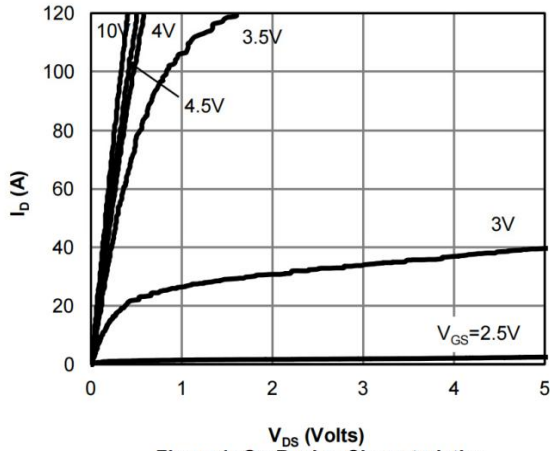


Figure 1: On-Region Characteristics

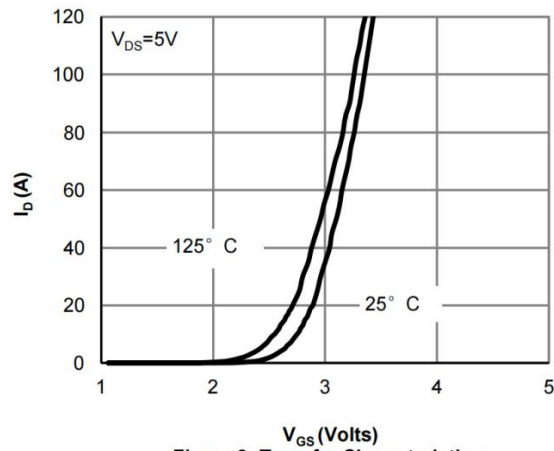


Figure 2: Transfer Characteristics

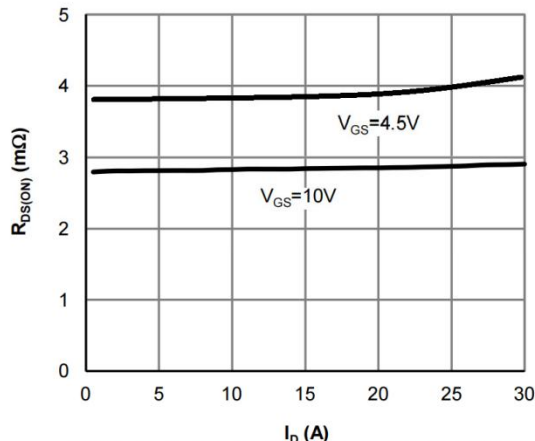


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

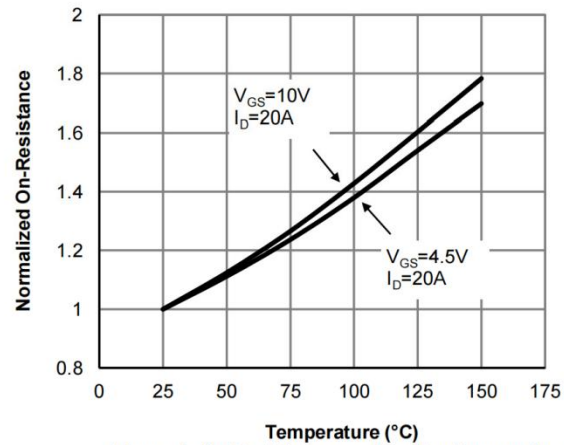


Figure 4: On-Resistance vs. Junction Temperature

Electrical Characteristic Curve

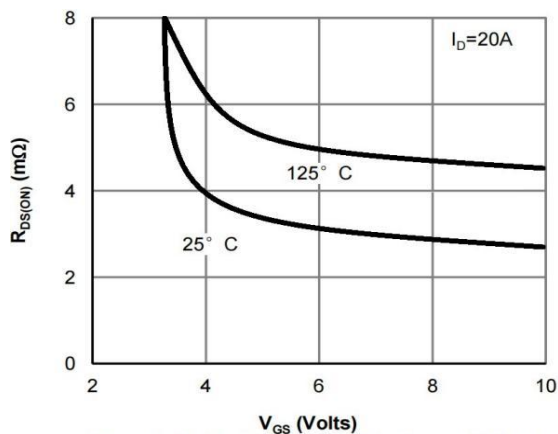


Figure 5: On-Resistance vs. Gate-Source Voltage

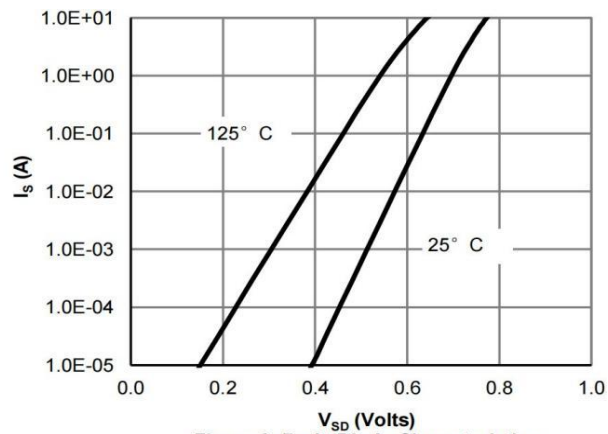
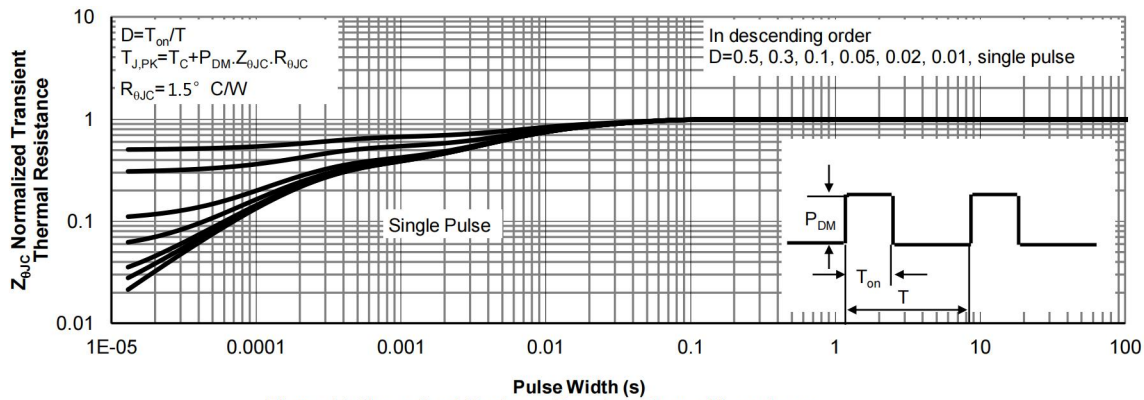
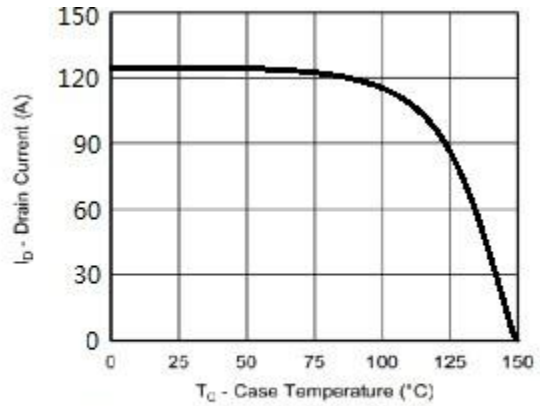
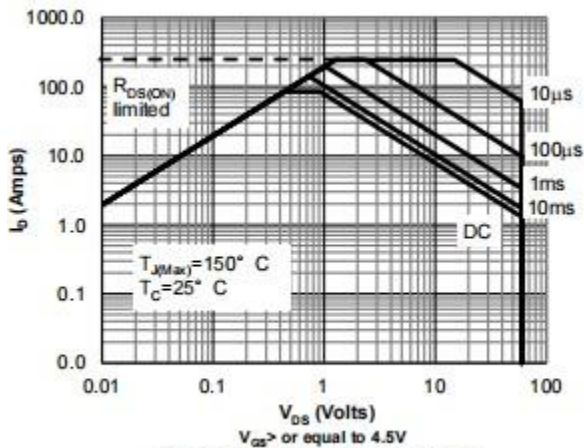
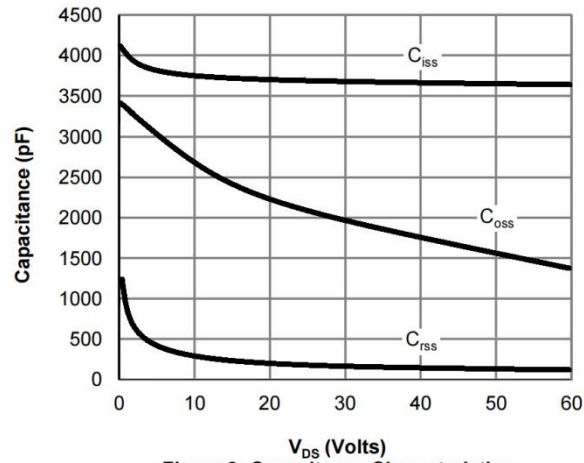
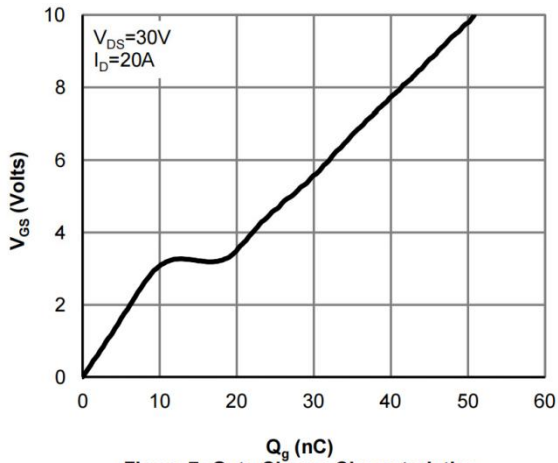
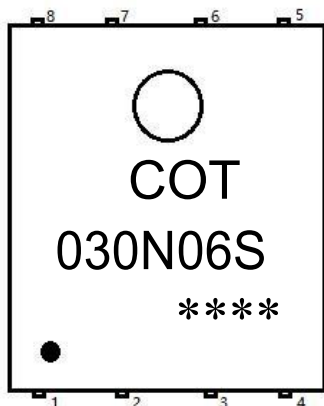


Figure 6: Body-Diode Characteristics





Note:

COT: Company Code.

030N06S: Product Type Code.

****: Lot No. Code, code change with Lot No.

Packaging SPEC.

REEL INFORMATION

Package Type	Units					Dimension (unit: mm ³)		
	Units/Reel	Reels/Inner Box	Units/Inner Box	Inner Boxes/Outer Box	Units/Outer Box	Reel	Inner Box	Outer Box
PDFN5×6	5000	2	10000	6	60000	13"×12	360×360×50	380×335×366

Package Outline Dimensions

PDFN5×6 外形尺寸图

PDFN5×6

Unit:mm

